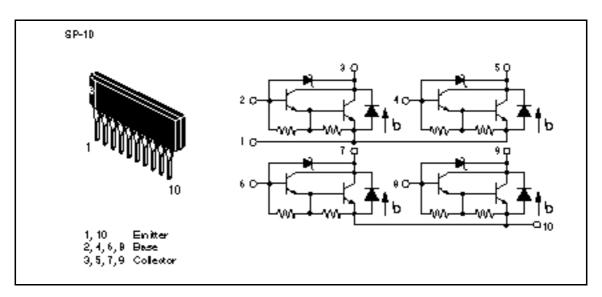
Silicon NPN Epitaxial

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Application

Low frequency power amplifier

Outline





Absolute Maximum Ratings (for each device, $Ta = 25^{\circ}C$)

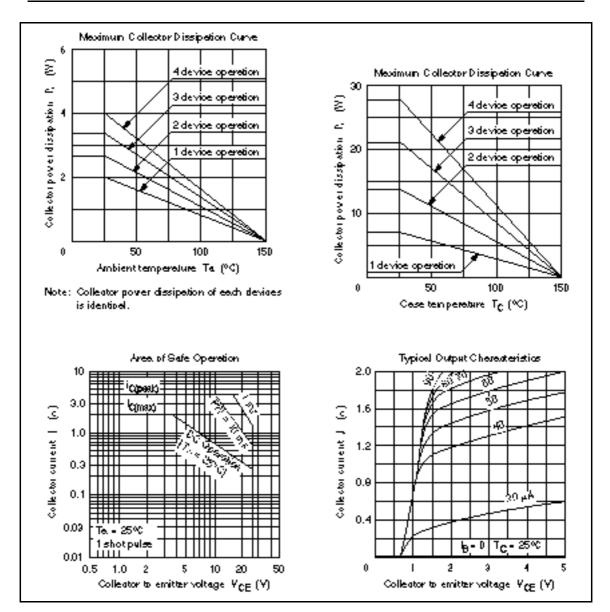
Symbol	Ratings	Unit
V _{CBO}	27	V
V _{CEO}	27	V
V _{EBO}	7	V
I _c	2	А
I _{C(peak)}	4	А
I _D	2	А
Pc*1	4	W
P_{c}^{*1} (T _c = 25°C)	28	_
Tj	150	°C
Tstg	–55 to +150	°C
	$ \begin{array}{r} V_{CBO} \\ V_{CEO} \\ V_{EBO} \\ I_{C} \\ I_{C(peak)} \\ I_{D} \\ P_{c}^{*1} \\ P_{c}^{*1} (T_{c} = 25^{\circ}C) \\ Tj $	$\begin{array}{c c} V_{CBO} & 27 \\ \hline V_{CEO} & 27 \\ \hline V_{CEO} & 7 \\ \hline I_{C} & 2 \\ \hline I_{C(peak)} & 4 \\ \hline I_{D} & 2 \\ \hline P_{C}^{*1} & 4 \\ \hline P_{C}^{*1} (T_{C} = 25^{\circ}C) & 28 \\ \hline Tj & 150 \\ \end{array}$

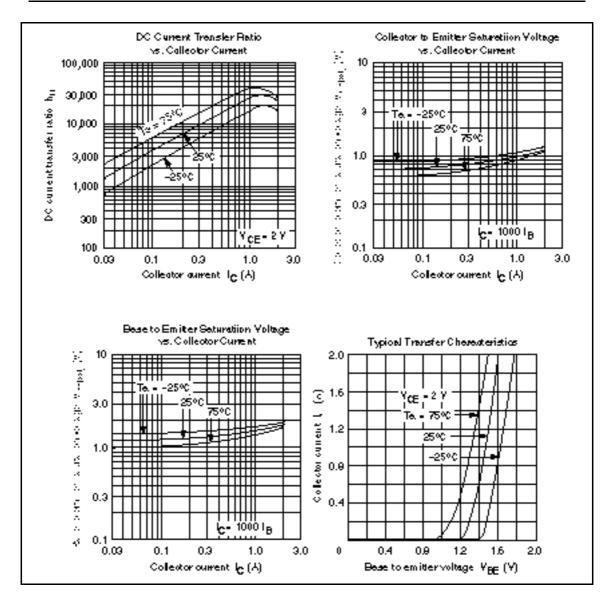
Note: 1. 4 devices operation.

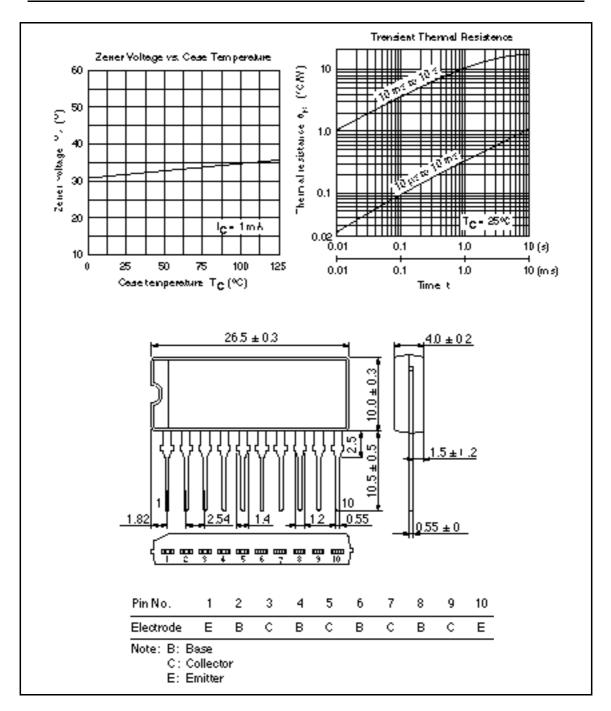
Electrical Characteristics (for each device, $Ta = 25^{\circ}C$)

Symbol	Min	Тур	Max	Unit	Test conditions
$V_{(BR)CBO}$	27	—	—	V	$I_{c} = 1 \text{ mA}, I_{E} = 0$
$V_{\text{CEO}(\text{SUS})}$	28	_	36	V	I_{c} = 1 A, L = 20 mH, R _{BE} =
$V_{(BR)EBO}$	7	_	—	V	$I_{\rm E} = 5$ mA, $I_{\rm C} = 0$
I _{CBO}		—	10	μA	$V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0$
I _{CEO}		—	10	-	V_{ce} = 20 V, R_{be} =
h _{FE}	7000	—	30000		$V_{ce} = 2 \text{ V}, \text{ I}_{c} = 0.5 \text{ A}$
h _{FE}	2000	_	_	-	$V_{ce} = 2 \text{ V}, \text{ I}_{c} = 2 \text{ A}^{*1}$
$V_{\text{CE(sat)}}$	_	_	1.5	V	$I_{c} = 2 \text{ A}, I_{B} = 2 \text{ mA}^{*1}$
$V_{BE(sat)}$			2.0	V	$I_{c} = 2 \text{ A}, I_{B} = 2 \text{ mA}^{*1}$
V _D			3.5	V	$I_{D} = 2 A$
	$V_{(BR)CBO}$ $V_{CEO(SUS)}$ $V_{(BR)EBO}$ I_{CBO} I_{CEO} h_{FE} h_{FE} $V_{CE(sat)}$ $V_{BE(sat)}$	$\begin{array}{c} V_{(BR)CBO} & 27 \\ \hline V_{CEO(SUS)} & 28 \\ \hline V_{(BR)EBO} & 7 \\ \hline I_{CBO} & \\ \hline I_{CEO} & \\ \hline h_{FE} & 7000 \\ \hline h_{FE} & 2000 \\ \hline V_{CE(sat)} & \\ \hline V_{BE(sat)} & \\ \end{array}$	V _{(BR)CBO} 27 — V _{CEO(SUS)} 28 — V _{(BR)EBO} 7 — I _{CBO} — — I _{CEO} — — I _{CEO} — — h _{FE} 7000 — h _{FE} 2000 — V _{CE(sat)} — —	$V_{(BR)CBO}$ 27 — — $V_{(BR)CBO}$ 28 — 36 $V_{(BR)EBO}$ 7 — — I_{CBO} — — 10 I_{CEO} — — 10 h_{FE} 7000 — 30000 h_{FE} 2000 — — $V_{CE(sat)}$ — — 1.5 $V_{BE(sat)}$ — — 2.0	$\begin{array}{c ccc} V_{(BR)CBO} & 27 & - & - & V \\ \hline V_{(CEO(SUS)} & 28 & - & 36 & V \\ \hline V_{(BR)EBO} & 7 & - & - & V \\ \hline I_{CBO} & - & - & 10 & \mu A \\ \hline I_{CEO} & - & - & 10 & \mu A \\ \hline I_{CEO} & - & - & 30000 & \\ \hline h_{FE} & 2000 & - & - & \\ \hline V_{CE(sat)} & - & - & 1.5 & V \\ \hline V_{BE(sat)} & - & - & 2.0 & V \\ \end{array}$

Note: 1. Pulse test.







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